NSN 5961-01-641-5820

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Inclosure Material:

Ceramic and metal

Overall Length:

Between 0.895 inches and 0.906 inches

Semiconductor Material:

Silicon alloy

Current Rating Per Characteristic:

10.0 milliamperes emitter current, instantaneous

Power Rating Per Characteristic:

583.0 watts total power dissipation

Product Name:

Rf and microwave transistor

Special Features:

Designed for high power pulse iff, dme, and tacan; applications; 200 w (typ.) iff 1030 - 1090 mhz; 150 w (min.) dme 1025 - 1150 mhz; 140 w (typ.) tacan 960 - 1215 mhz; 8.2 db gain; refractory gold metallization; ballasting andlow thermal resistance for reliability and ruggedness; 30: 1 load vswr capability at specified operating conditions;

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

A110a0